

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL To Commissioner For Patents Enclosed herewith is a Form PTO-1449, any required copies of documents listed thereon, and any concise explanation of their relevance is indicated below per 37 CFR 1.97.	Application Number	10/550,853
	Filing Date	09/22/05
	First Named Inventor	PHILIPPE MEUNIER-BEILLARD
	Group Art Unit	2823
	Examiner Name	Khiem D. Nguyen
	Atty. Docket Number	NL03 0357 US1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number No.-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear
/KN/		US- 2003/003646	01-02-2003	DE BOER WIEBE BARTELD	
↓		US- 6 251 188	06-26-2001	OKUBO KAZUYA ET AL	
		US- 5 378 651	01-03-1995	AGNELLO ET AL	
/KN/		US- 6 251 188	6-26-2001	HASHIMOTO ET AL	
		US-			
		US-			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number (ctry ² -no. ⁴ -kind ⁵ , if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of cited document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
/KN/		EP 0 459 122	12-04-1991	MEYERSON, BERNARD S.		

NON-PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in capital letters), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ⁶
/KN/		ALONSO J C: "LOW-TEMPERATURE EPITAXIAL GROWTH OF UNDOPED AND N-DOPED SILICON BY PHOTOCHEMICAL VAPOR DEPOSITION USING SIH4/SIH2/H2/PH3 MIXTURES" THIN SOLID FILM, ELSEVIER-SEQUOIA S.A. LAUSANNE, CH, VOL. 327, NO. 1/2, 1994, PAGES 98-104		

Examiner Signature	/Khiem Nguyen/	Date Considered	03/22/2007
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the